

FORM 1449*

INFORMATION DISCLOSURE STATEMENT

IN AN APPLICATION

(Use several sheets if necessary)

Docket Number:
STFD.003C4Application Number:
10/777,453

Applicant: NEMATI et al.

Filing Date: 2/12/2004

Group Art Unit: 2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	6,727,529	04/27/2004	Nemati et al.			
	6,528,356	03/04/2003	Nemati et al.			
	6,448,586	09/10/2002	Nemati et al.			
	6,229,161	05/08/2001	Nemati et al.			
	5,981,984	11/09/1999	Iwaana et al.			
	5,939,736	08/17/1999	Takahashi			
	5,936,267	08/10/1999	Iwamuro			
	5,914,503	06/22/1999	Iwamuro et al.			
	5,910,738	06/08/1999	Shinohe et al.			
	5,874,751	02/23/1999	Iwamuro et al.			
	5,689,458	11/18/1997	Kuriyama			
	5,587,944	12/24/1996	Shen et al.			
	5,543,652	08/06/1996	Ikeda et al.			
	5,525,820	06/11/1996	Furuyama			
	5,471,419	11/28/1995	Sankaranarayanan et al.			
	5,464,994	11/07/1995	Shinohe et al.			
	5,412,598	05/02/1995	Shulman			
	5,396,454	03/07/1995	Nowak			
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	5,321,285	06/14/1994	Lee et al.			
	4,959,703	09/25/1990	Ogura et al.			
	4,677,455	06/30/1987	Okajima			
	4,612,448	09/16/1986	Strack			
	4,590,589	05/20/1986	Gerzberg			
	4,146,902	03/27/1979	Tanimoto et al.			
	4,090,254	05/16/1978	Ho et al.			
	3,986,177	10/12/1976	Picquendar et al.			
TTN	3,918,033	11/04/1975	Case et al.			

EXAMINER

DATE CONSIDERED

3/4/2005

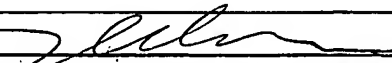
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
TTN	JP 57 208177 A	21 Dec. 1982	Japan			X	
TTN	FR 2 110 326 A	2 June 1972	France				X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TTN	1999	F. Nemati and J.D. Plummer, <i>A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories</i> , Center for Integrated Systems, Stanford University, Stanford, CA, 1999.
✓	6/1998	F. Nemati and J.D. Plummer, <i>A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device</i> , Center for Integrated Systems, Stanford University, Stanford, CA 94305.
		F. Nemati and J.D. Plummer, <i>A Novel Vertical Storage SRAM Cell</i> , Student Paper written for Center for Integrated Systems, Stanford University, Stanford, CA 94305.
	1987	Baliga, B. Jayant, <i>Modern Power Devices</i> , pp. 349-350.
	1981	S. M. Sze, <i>Physics of Semiconductor Devices Second Edition</i> , John Wiley & Sons, pp. 198-209, 1981.
TTN	2/1980	Plummer, James D. and Scharf, Brad W., <i>Insulated-Gate Planar Thyristors: I-Structure and Basic Operation</i> , pp. 380-386.

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